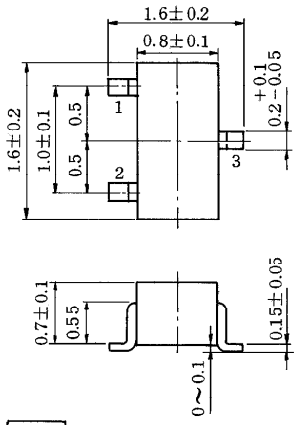
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

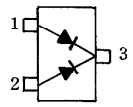
1SS385

HIGH SPEED SWITCHING.

Unit in mm

- Low Forward Voltage : $V_{F(2)}$ = 0.23V (Typ.) @I_F = 5mA
- Small Package





SSM

1. ANODE
2. ANODE
3. CATHODE

JEDEC	—
EIAJ	—
TOSHIBA	1-2S1B

Weight : 2.4mg

MAXIMUM RATINGS (Ta = 25°C)

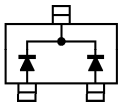
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200※	mA
Average Forward Current	I_O	100※	mA
Surge Current (10ms)	I_{FSM}	1※	A
Power Dissipation	P	100	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C
Operating Temperature Range	T_{opr}	−40~100	°C

※ : Unit Rating. Total Rating = Unit Rating × 1.5

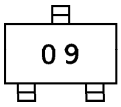
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F = 1mA	—	0.18	—	V
	$V_{F(2)}$	I_F = 5mA	—	0.23	0.30	V
	$V_{F(3)}$	I_F = 100mA	—	0.35	0.50	V
Reverse Current	I_R	V_R = 10V	—	—	20	μA
Total Capacitance	C_T	V_R = 0, f = 1MHz	—	20	40	pF

EQUIVALENT CIRCUIT (TOP VIEW)



Marking



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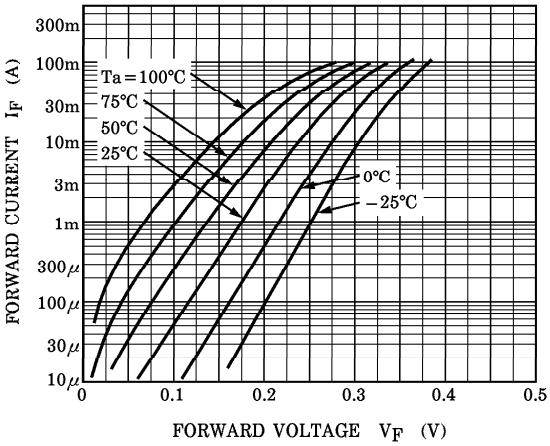
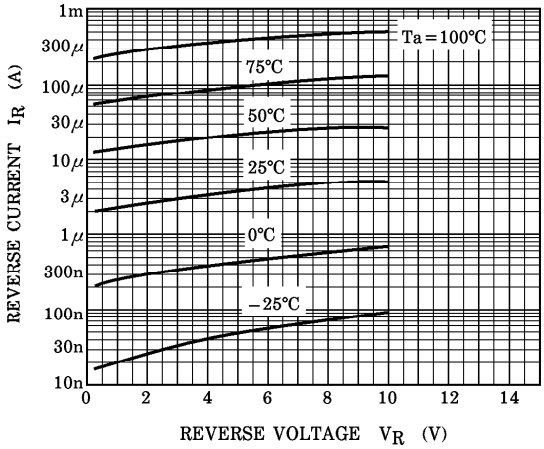
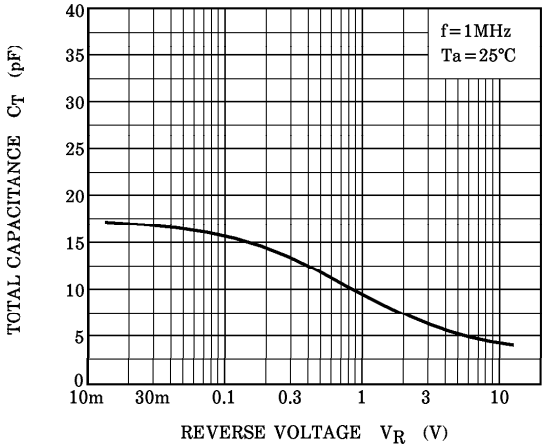
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



P – Ta